



# Nano-sized ceria abrasive for advanced polishing applications in IC manufacturing

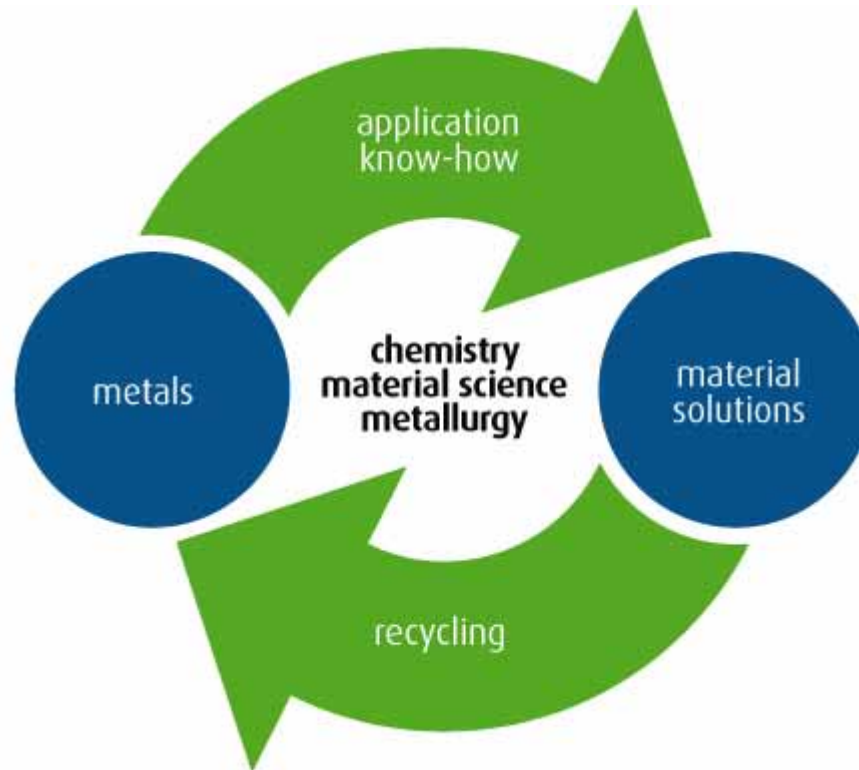
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# Outline

- Introducing Umicore nanomaterials
- Nano-powder synthesis
- Dispersion technology
- Case study – nano-ceria for CMP applications
  - CMP application
  - Development of nano-ceria for CMP
- Summary & conclusions

## The Umicore approach to materials technology



# Introducing Umicore

## Umicore today provides ...

- the **automotive catalysts** for almost 1 in 4 cars produced in the world
- key materials for the **rechargeable batteries** for more than 30% of all cell phones and laptops sold this year
- the **semiconductor substrates** for more than 60% of all **satellite solar cells** in the last 2 years
- **recycling services** for electronic scrap, batteries and spent catalysts to gain over 20 different metals

## Umicore in a nutshell ...

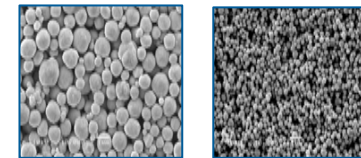
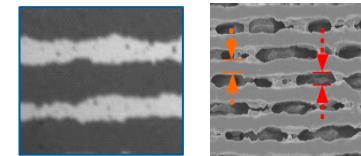
- **15,000** people
- **50** industrial locations worldwide
- **1.9 B €** revenue in 2006



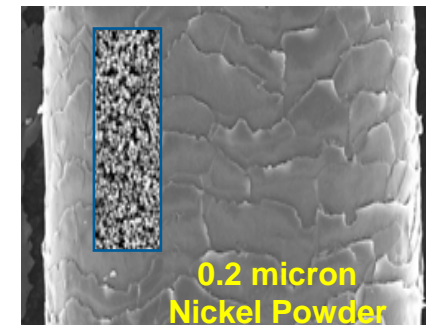
## Nano: Hype or future?

- Umicore started nano activities ~ 8 years ago
- Nano creates a Win<sup>3</sup> situation:
  - Device maker:
    - Miniaturisation (e.g. MLCC)
    - Enables new technologies
  - Supplier:
    - Added value products
    - Decommoditisation
  - Society:
    - Sustainability: more function with less materials

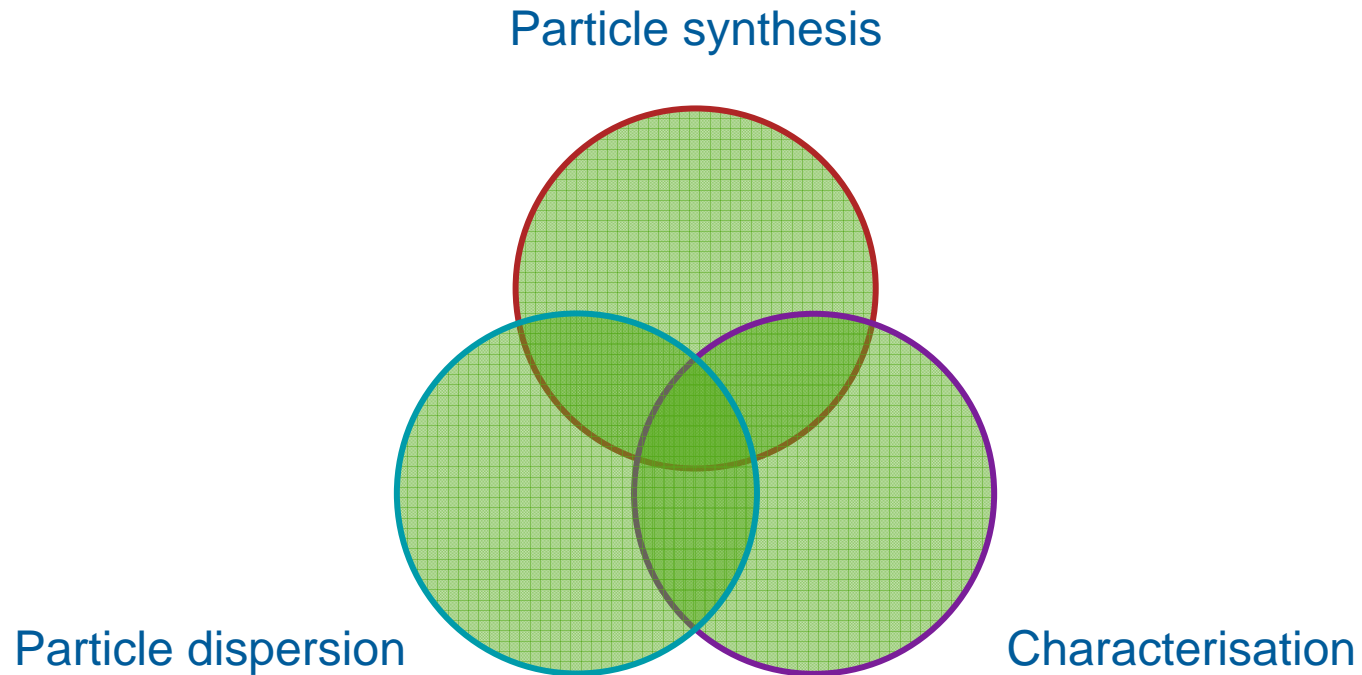
### Technology miniaturization



### Materials miniaturization



# Technology development for nanomaterials production



# Powder synthesis



## Particle synthesis and development

Particles or functional particles are developed in function of the application

- Functionality
- Quality
- Cost

On the basis of this, a synthesis technology is developed, Umicore has developed a range of synthesis and production technologies for the development of nanomaterials

- Gas phase synthesis (evaporation + reaction + quenching)
  - Mainly for oxide materials
- Precipitation techniques
- Milling techniques



## Umicore precipitation Technology

- large economy of scale
- patented process



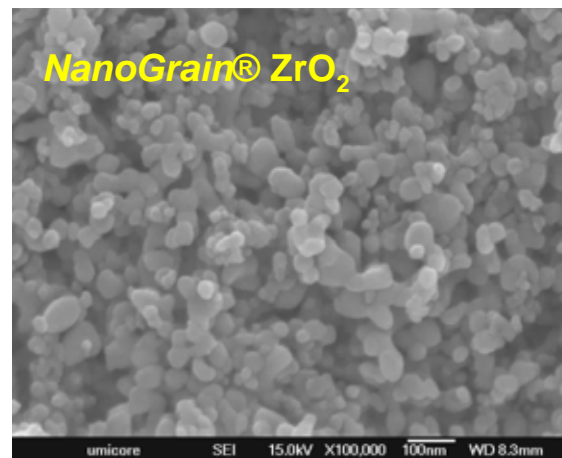
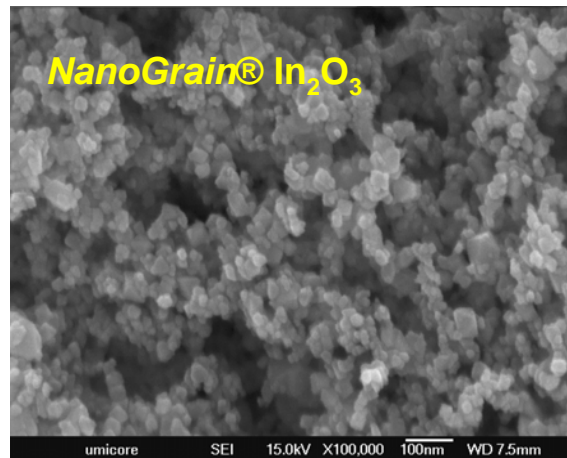
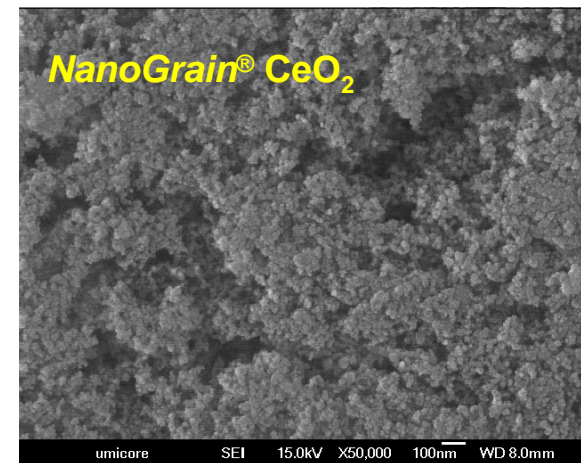
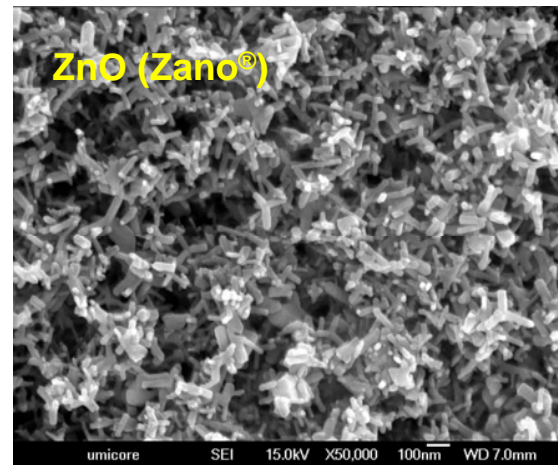
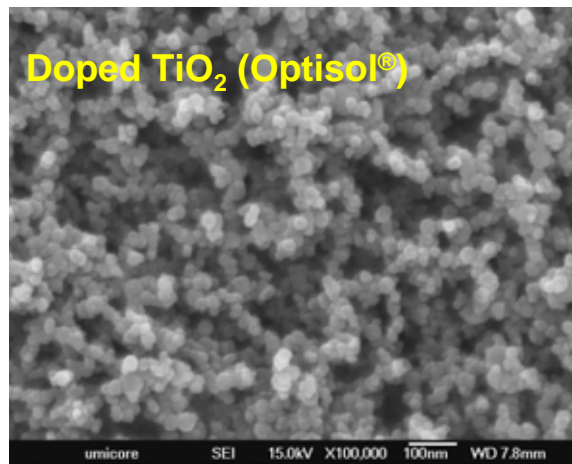
Process:

Metal solution + reduction



Precipitated Metal

## Umicore NanoMaterials particles, oxides



### Others

Anatase, Rutile, GeO<sub>2</sub>,  
ITO, doped ZnO, Al<sub>2</sub>O<sub>3</sub>,

...

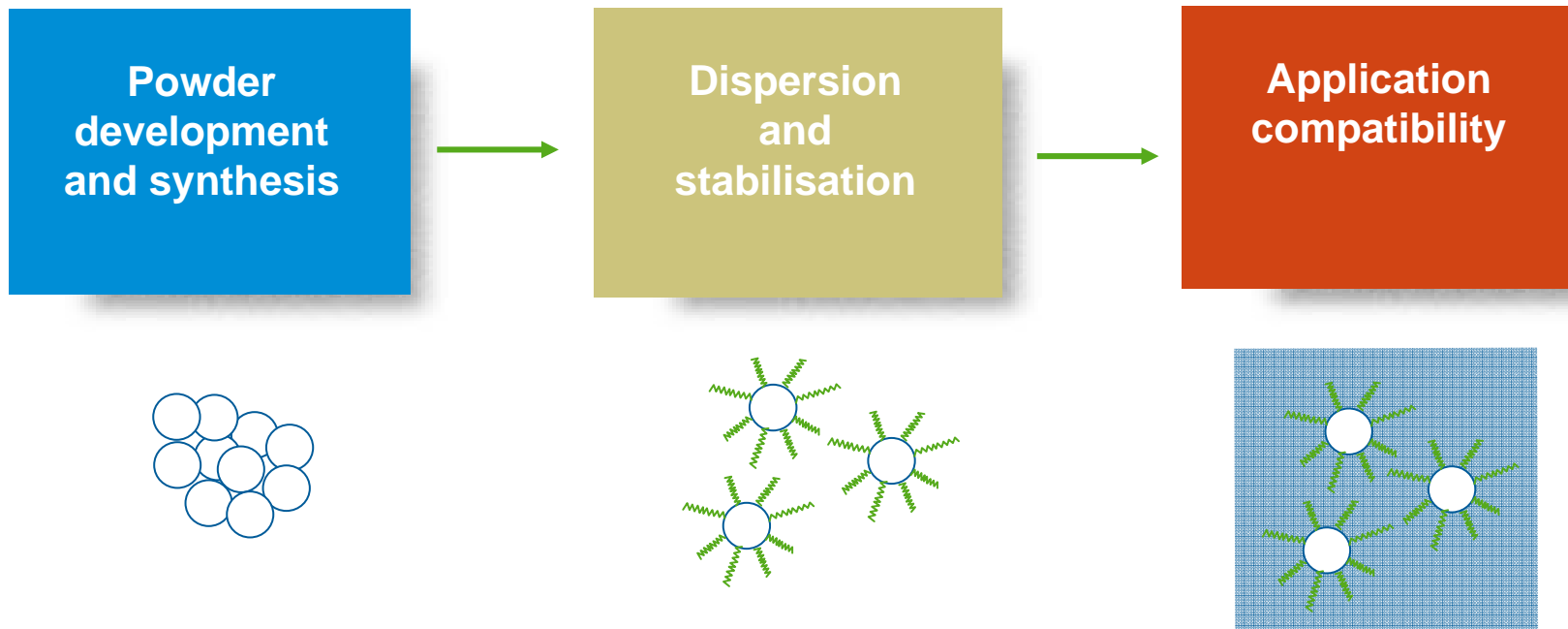
*materials for a better life*

# Dispersion technology



## Dispersion technology

- Dispersion technology is key link to the application



## Dispersion technology

- De-agglomeration of particles:
  - Apply the right amount of energy to obtain desired results

### Low

- Used to prepare pre-mixes
- De-agglomeration not optimal
- Examples:
  - dissolver

### Intermediate

- Low solids loading
- De-agglomeration
- Examples:
  - ultrasonication
  - rotor-stator

### High

- High solids loading
- De-agglomeration and milling
- Examples:
  - bead mills
  - ball mills

- Stabilisation e.g. with additives – need for compliance with application!

Case study:

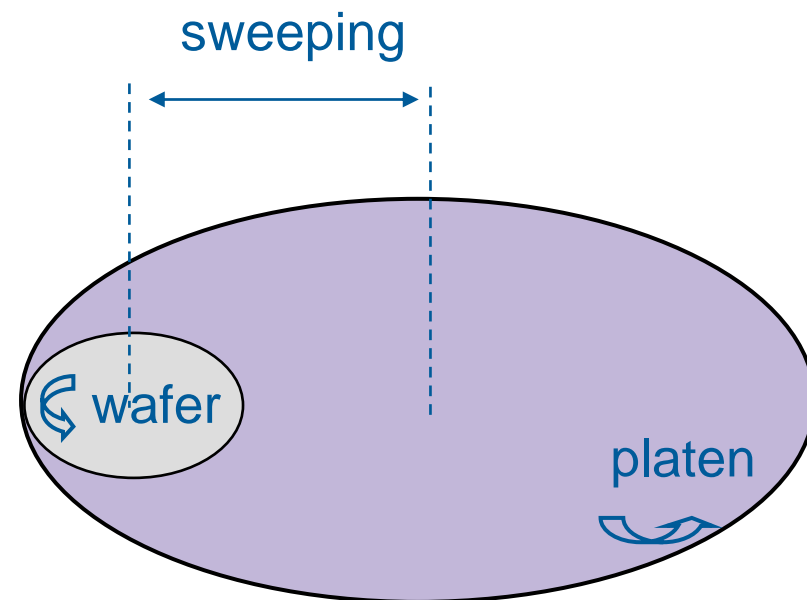
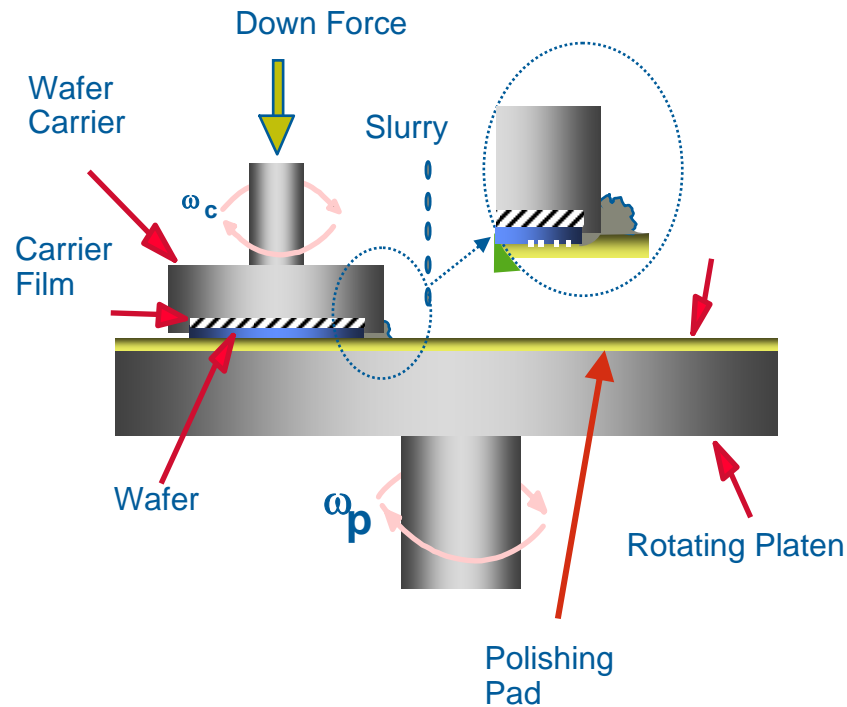
Nano-ceria for  
CMP applications

1 – CMP application



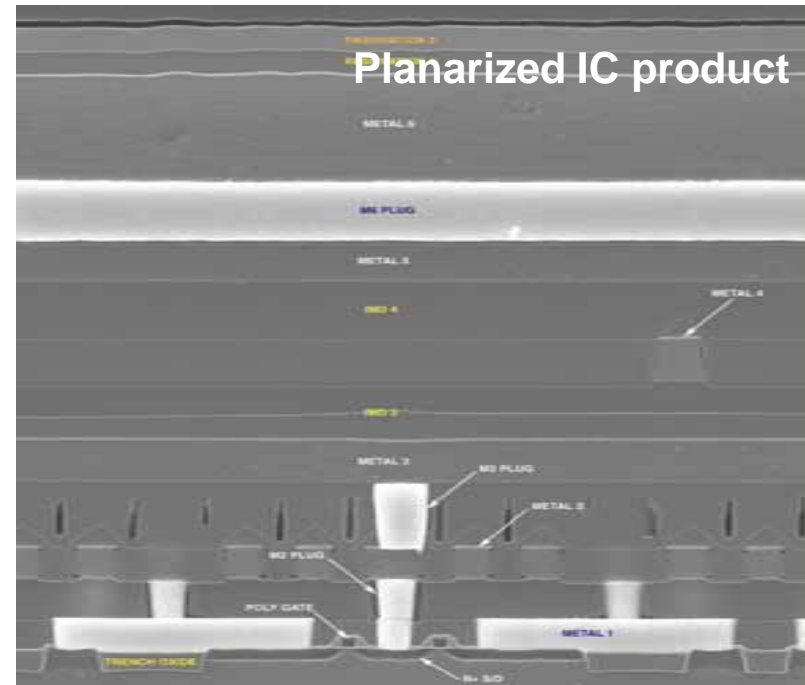
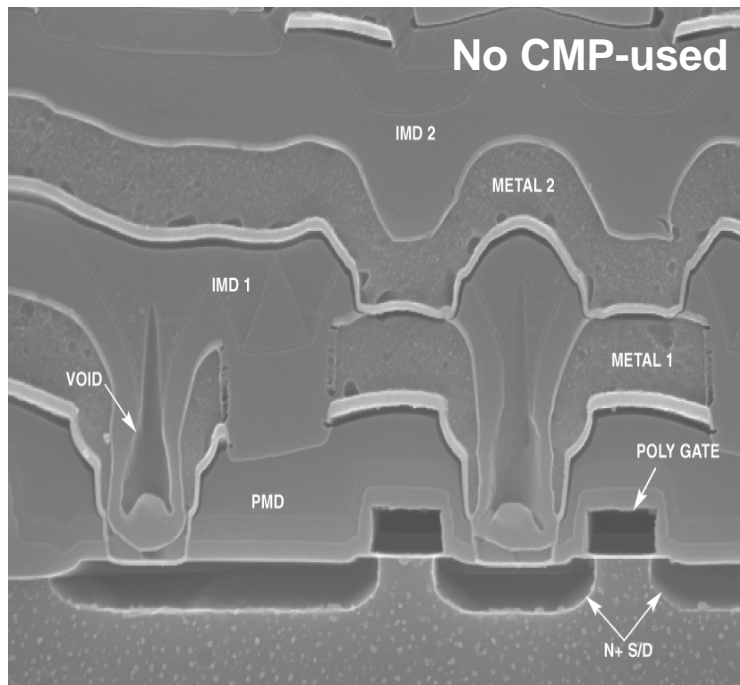
## Chemical mechanical planarization (CMP)

- A technology used in the manufacturing of integrated circuits (IC's)
- Wafer is pushed against a polishing pad
- Pad and wafer rotate
- A polishing slurry is continuously fed to the process
- The slurry contains nanoparticles



## CMP: an enabling technology in IC manufacturing

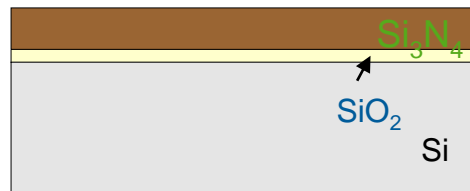
- More and smaller transistors on single chip = increasing # interconnecting layers
- Accumulated topology of different layers exceeds lithography depth of focus
- Solution is planarisation of layers by CMP, invented by IBM in the 1980's
- Developed into enabler for many of the new technologies in e.g. Intel's processors





# Example: shallow trench isolation (STI)

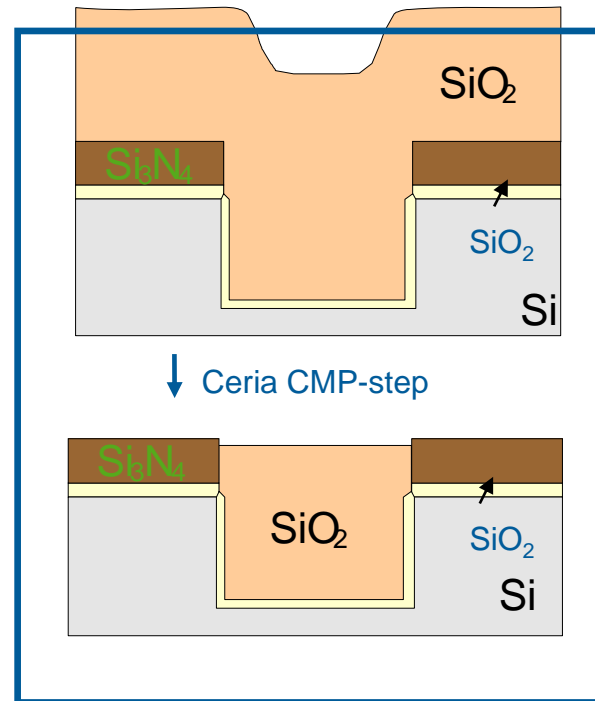
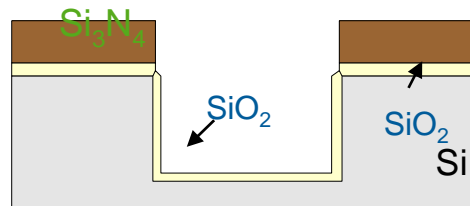
Field oxide deposition



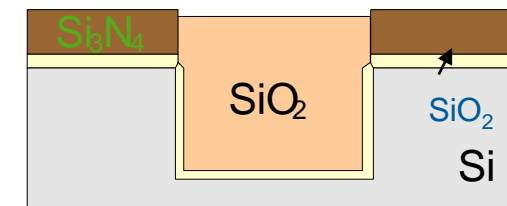
Mask active areas and etch trench



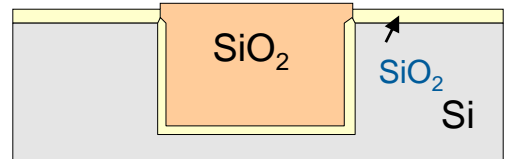
Pre-oxidize trench



Ceria CMP-step



Wet nitride etch



STI CMP slurries contain ceria

Case study:

Nano-ceria for  
CMP applications

2 – Development of nano-  
ceria for CMP



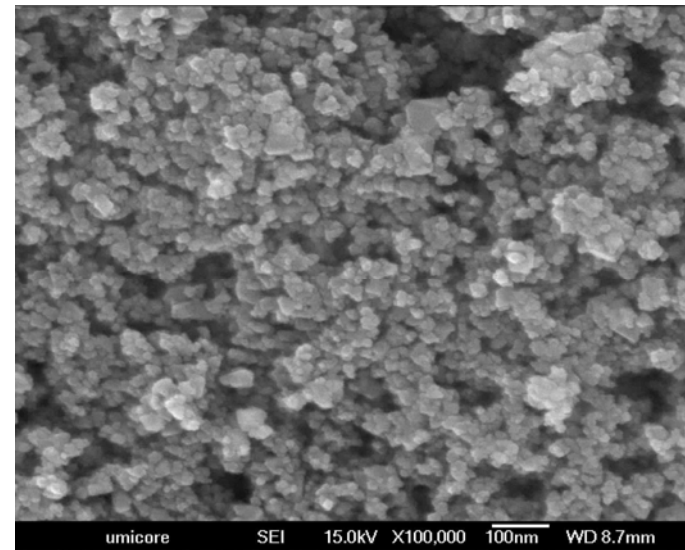
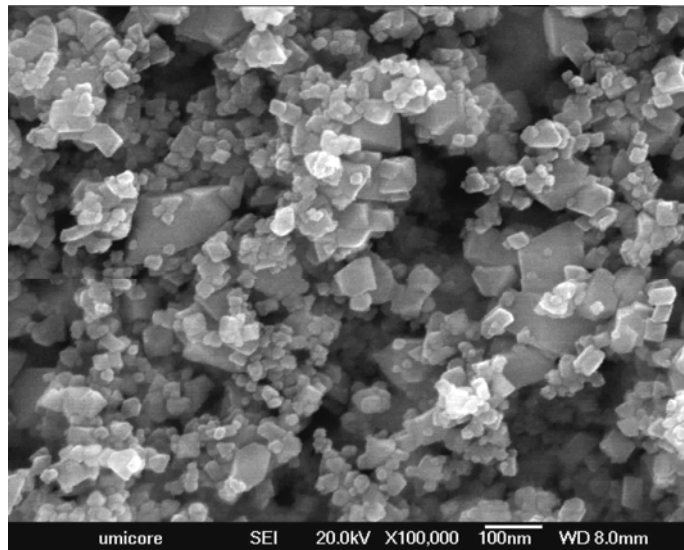
## Objective and approach

### Development of ceria particles with low defectivity for STI CMP

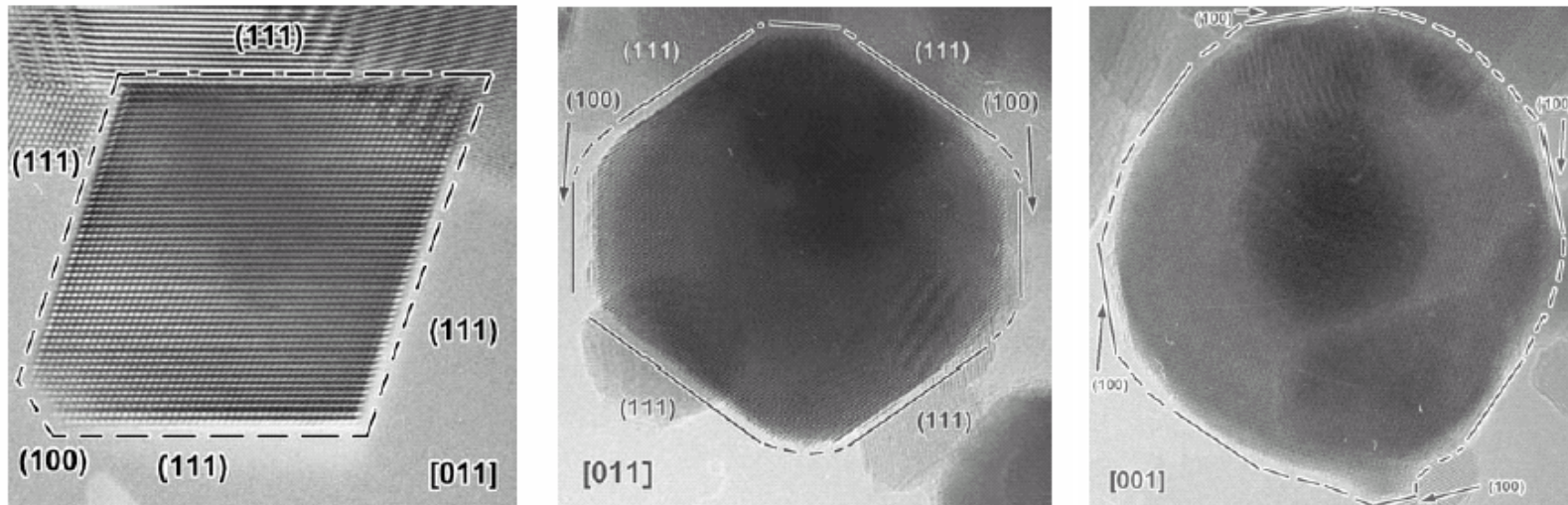
- Development of synthesis route to control ceria properties
- Testing of ceria particles with different properties in CMP
  - Impact of specific surface area
  - Impact of large particle tail
  - Impact of particle shape
- Feedback of CMP results to synthesis
- Establishment of consistency for best product

## Ceria particle size/specific surface area

- Specific surface area in range 20 to 85 m<sup>2</sup>/g  
Equivalent average primary particle size range: 10 to 40 nm
- Primary particles not sintered: no hard agglomerates
- 100 % cubic crystalline



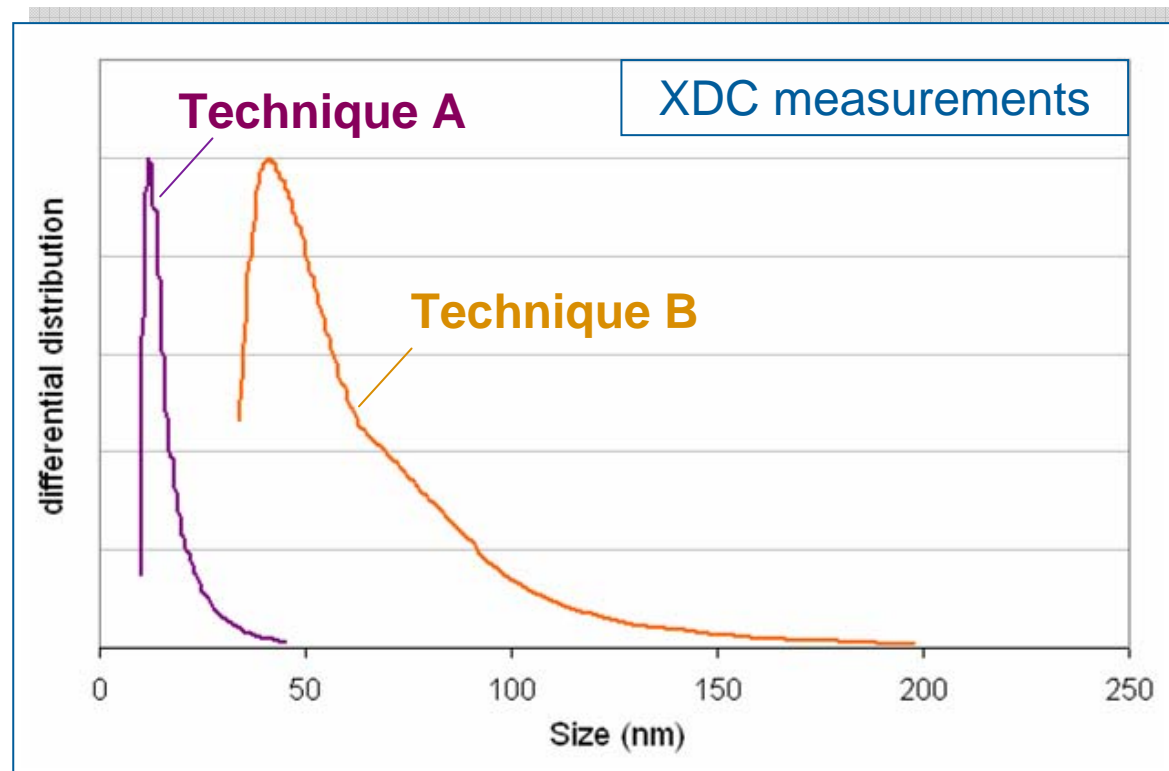
## Control of particle morphology



Particle morphology can be controlled through processing conditions

## Ceria dispersion properties

Particle size distribution in dispersion determined by dispersion technique used

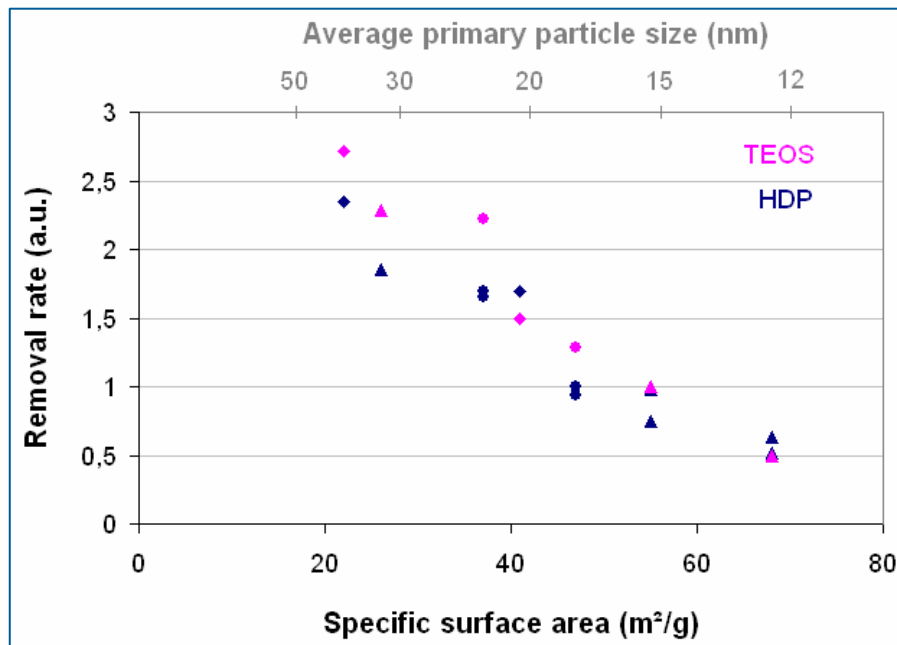


## CMP evaluation

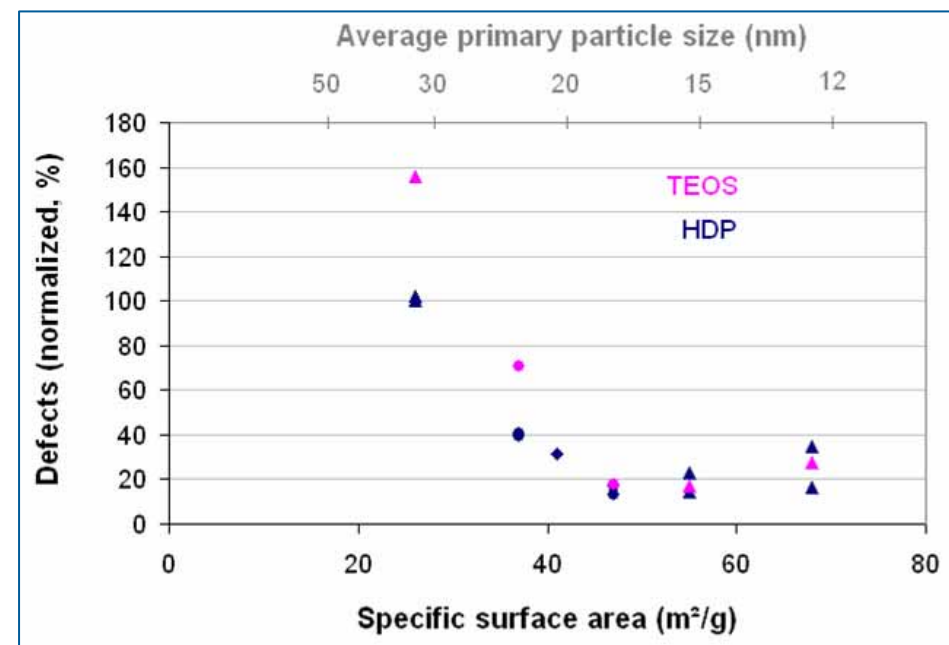
- Key performance parameters for STI CMP
  - High removal rate for SiO<sub>2</sub>
  - Smooth, defect free surface finish (= low defectivity)
- Stabilizer added to dispersions (no other additives)
- Pre and post CMP characterization
  - Film thickness: spectroscopic ellipsometry (ASET-F5, KLA Tencor)
  - Defectivity: dark field laser light scattering (SP-1, KLA Tencor)
- Defectivity evaluation
  - Minimum defect size 0.15 μm
  - Focus on scratches as particles can be removed during further processing

## Impact of specific surface area

### Removal rate



### Defectivity

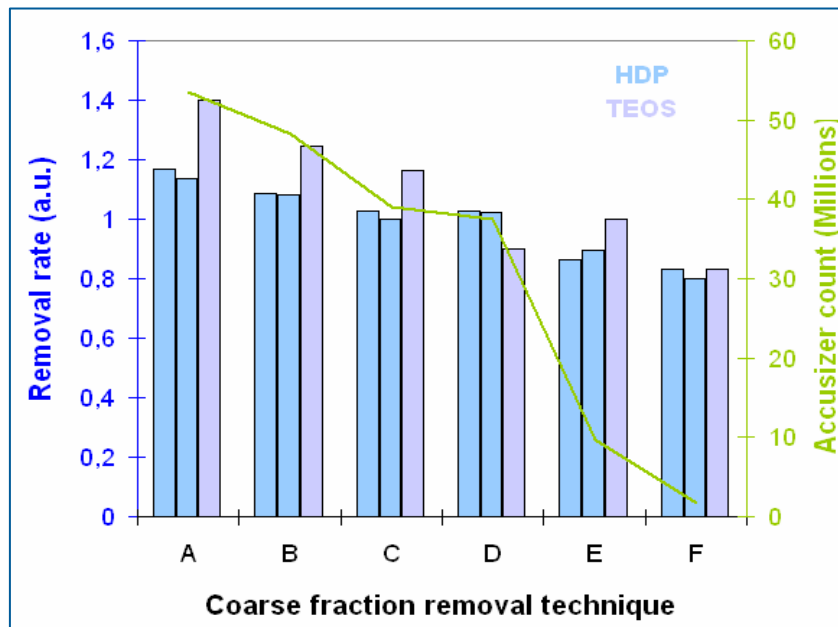


- Strong correlation between particle size and removal rate
- Lower defectivity for smaller particle size, but plateau below 20 nm

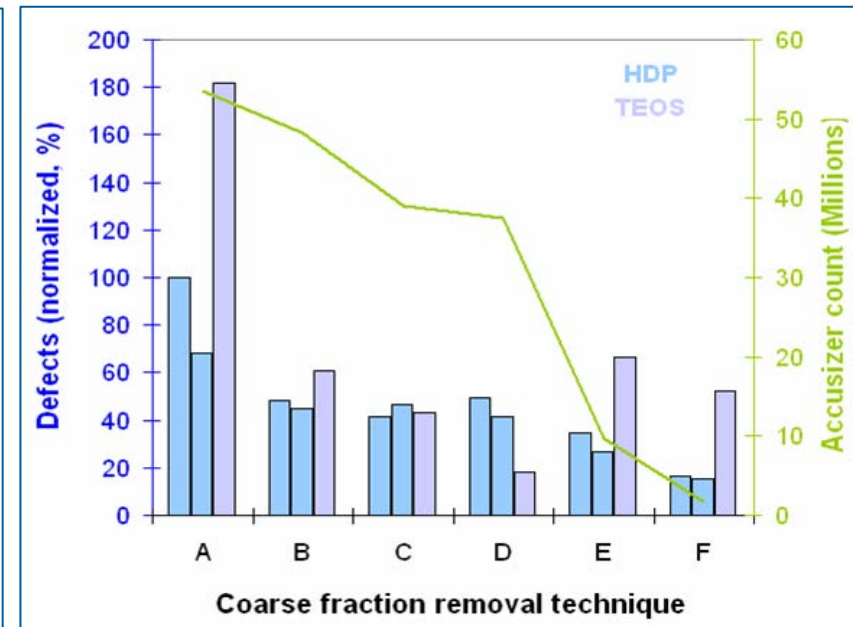


# Effect of various coarse fraction removal techniques on large particle count and polishing results

Removal rate



Defectivity



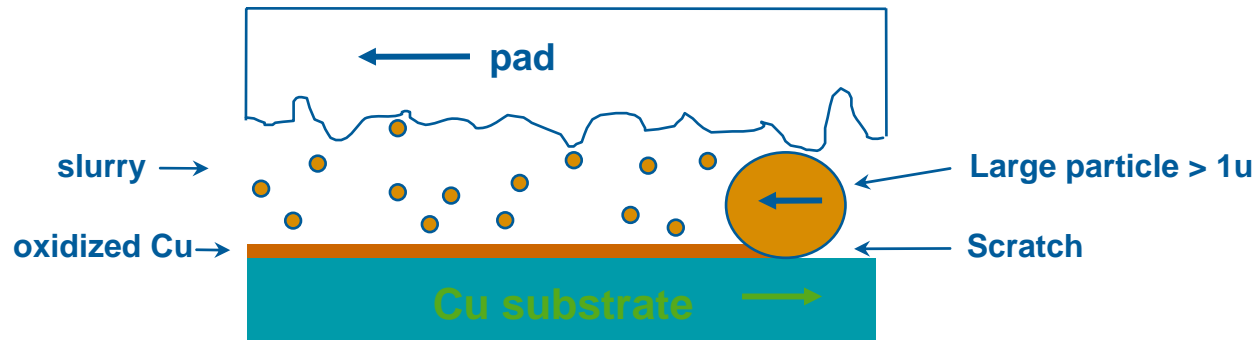
A : reference (as sonicated)

B..F : different techniques

- Large particle count controlled by coarse fraction removal technique

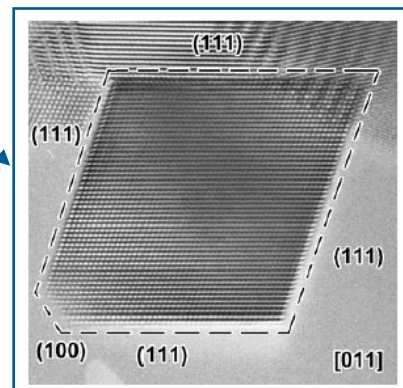
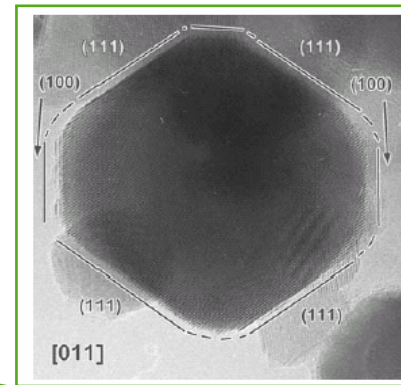
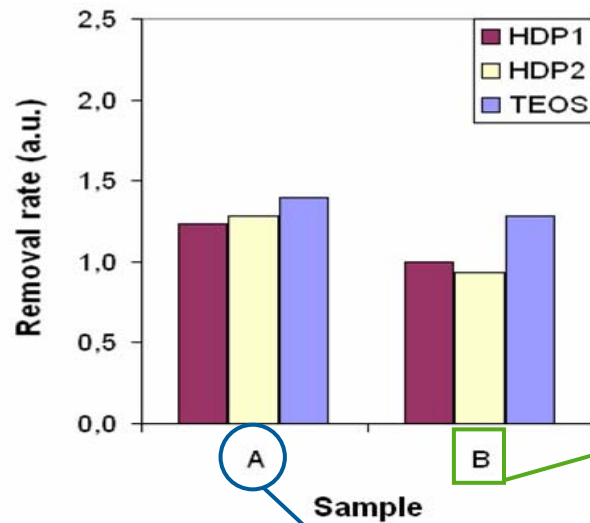
## Importance of large particle count for defects

### CMP Scratch Formation

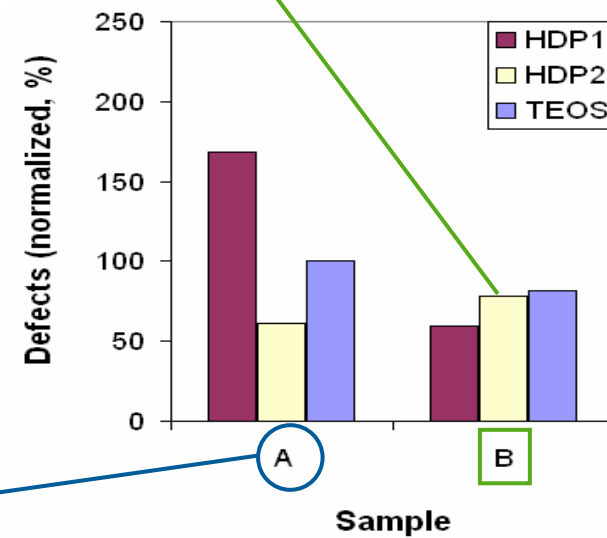


- ◆ Unwanted large particles dig too deep
- ◆ Damage causing particles cannot be easily detected
- ◆ Excellent control of large particle tail required!

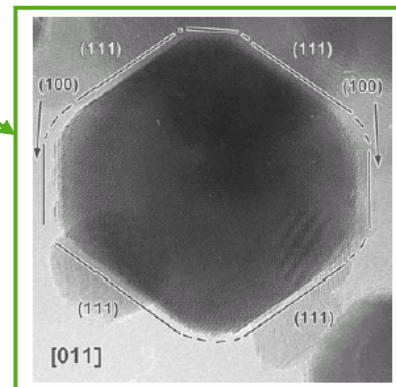
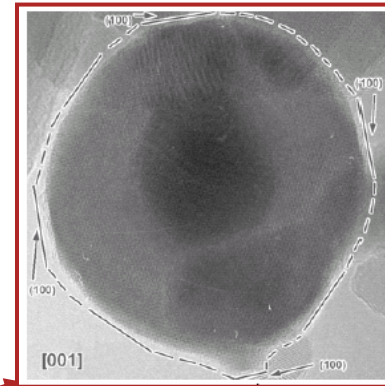
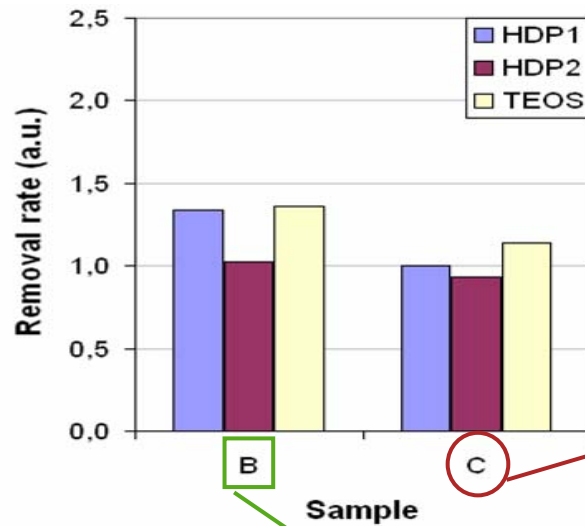
# Impact of particle shape I



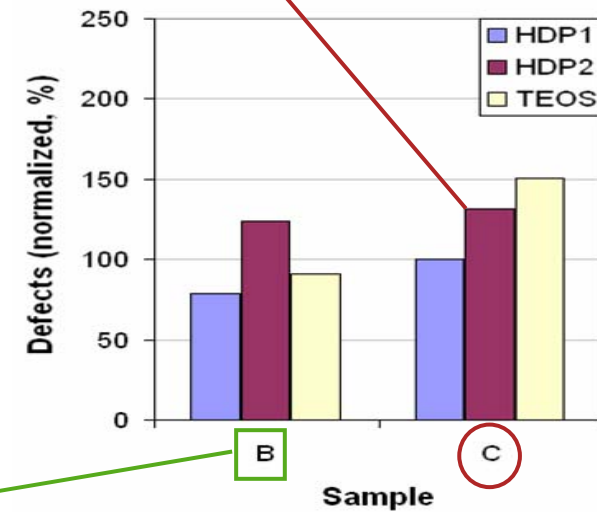
Sharp particles have slightly better CMP performance than truncated particles



## Impact of particle shape II

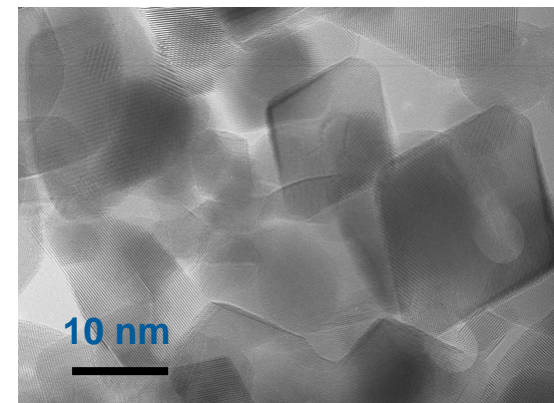
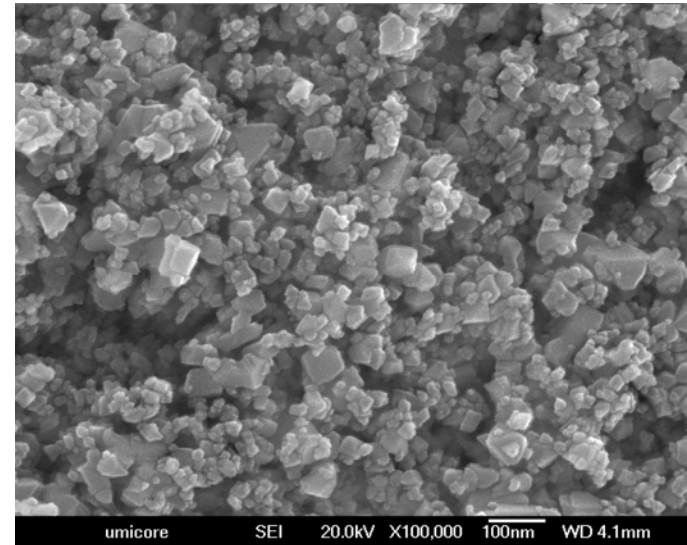


Rounded particles  
lower removal rate  
& higher defectivity  
Unexpected result!

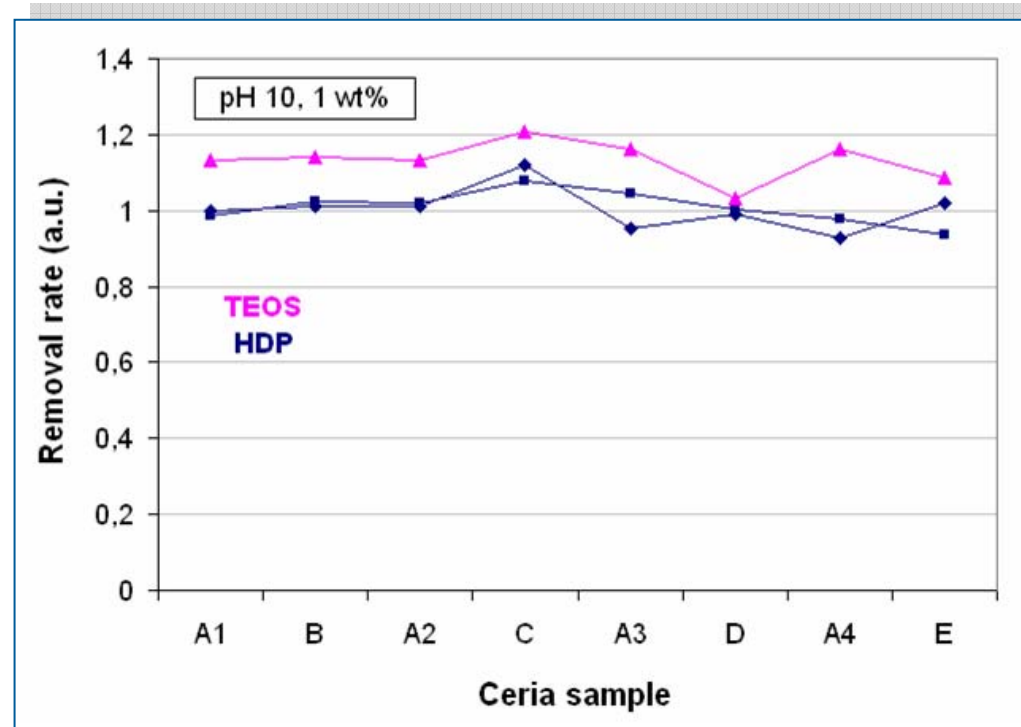


## Final selected product

- Adjusted particle size
- Controlled large particle tail
- Controlled morphology
  
- Excellent combination of removal rate and defectivity
  
- Excellent reproducibility
- Low cost potential



## Consistency



- 5 Production batches (A thru E) tested in CMP
- Good consistency of CMP results

## Summary and conclusions

- Development of new nanomaterials for large scale production requires dispersion and application knowledge
- Gas phase synthesis process was developed to gain flexible control over particle size, distribution and morphology
- Nano-ceria particles for CMP were developed allowing
  - Better defectivity
  - Good removal rate
  - Good batch-to-batch and within-batch consistency



Thank You

i-SUP 2008  
April 24th 2008

Contact NanoGrain<sup>®</sup>  
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